Intel - EP1S80F1508C5 Datasheet





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Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	7904
Number of Logic Elements/Cells	79040
Total RAM Bits	7427520
Number of I/O	1022
Number of Gates	-
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	1508-BBGA, FCBGA
Supplier Device Package	1508-FBGA, FC (40x40)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep1s80f1508c5

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Chapter	Date/Version	Changes Made
2	July 2005 v3.2	 Added "Clear Signals" section. Updated "Power Sequencing & Hot Socketing" section. Format changes.
	September 2004, v3.1	 Updated fast regional clock networks description on page 2–73. Deleted the word preliminary from the "specification for the maximum time to relock is 100 µs" on page 2–90. Added information about differential SSTL and HSTL outputs in "External Clock Outputs" on page 2–92. Updated notes in Figure 2–55 on page 2–93. Added information about <i>m</i> counter to "Clock Multiplication & Division" on page 2–101. Updated Note 1 in Table 2–58 on page 2–101. Updated description of "Clock Multiplication & Division" on page 2–88. Updated Table 2–22 on page 2–102. Added references to AN 349 and AN 329 to "External RAM Interfacing" on page 2–116: updated the table, updated Notes 3 and 4. Notes 4, 5, and 6, are now Notes 5, 6, and 7, respectively. Updated Table 2–26 on page 2–117. Added information about PCI Compliance to page 2–120. Table 2–32 on page 2–126: updated the table and deleted Note 1. Updated reference to device pin-outs now being available on the web on page 2–130. Added Notes 4 and 5 to Table 2–36 on page 2–131. Updated Note 5 in Table 2–37 on page 2–131. Updated Note 5 in Table 2–41 on page 2–135.
	April 2004, v3.0	 Added note 3 to rows 11 and 12 in Table 2–18. Deleted "Stratix and Stratix GX Device PLL Availability" table. Added I/O standards row in Table 2–28 that support max and min strength. Row clk [1,3,8,10] was removed from Table 2–30. Added checkmarks in Enhanced column for LVPECL, 3.3-V PCML, LVDS, and HyperTransport technology rows in Table 2–32. Removed the Left and Right I/O Banks row in Table 2–34. Changed RCLK values in Figures 2–50 and 2–51. External RAM Interfacing section replaced.
	November 2003, v2.2	 Added 672-pin BGA package information in Table 2–37. Removed support for series and parallel on-chip termination. Termination Technology renamed differential on-chip termination. Updated the number of channels per PLL in Tables 2-38 through 2-42. Updated Figures 2–65 and 2–67.
	October 2003, v2.1	 Updated DDR I information. Updated Table 2–22. Added Tables 2–25, 2–29, 2–30, and 2–72. Updated Figures 2–59, 2–65, and 2–67. Updated the Lock Detect section.

dedicated clocks, these registers provide exceptional performance and interface support with external memory devices such as DDR SDRAM, FCRAM, ZBT, and QDR SRAM devices.

High-speed serial interface channels support transfers at up to 840 Mbps using LVDS, LVPECL, 3.3-V PCML, or HyperTransport technology I/O standards.

Figure 2–1 shows an overview of the Stratix device.





asynchronous load, and clear signals. An asynchronous clear signal takes precedence if both signals are asserted simultaneously. Each LAB supports up to two clears and one preset signal.

In addition to the clear and preset ports, Stratix devices provide a chipwide reset pin (DEV_CLRn) that resets all registers in the device. An option set before compilation in the Quartus II software controls this pin. This chip-wide reset overrides all other control signals.

MultiTrack Interconnect

In the Stratix architecture, connections between LEs, TriMatrix memory, DSP blocks, and device I/O pins are provided by the MultiTrack interconnect structure with DirectDrive™ technology. The MultiTrack interconnect consists of continuous, performance-optimized routing lines of different lengths and speeds used for inter- and intra-design block connectivity. The Quartus II Compiler automatically places critical design paths on faster interconnects to improve design performance.

DirectDrive technology is a deterministic routing technology that ensures identical routing resource usage for any function regardless of placement within the device. The MultiTrack interconnect and DirectDrive technology simplify the integration stage of block-based designing by eliminating the re-optimization cycles that typically follow design changes and additions.

The MultiTrack interconnect consists of row and column interconnects that span fixed distances. A routing structure with fixed length resources for all devices allows predictable and repeatable performance when migrating through different device densities. Dedicated row interconnects route signals to and from LABs, DSP blocks, and TriMatrix memory within the same row. These row resources include:

- Direct link interconnects between LABs and adjacent blocks.
- **R**4 interconnects traversing four blocks to the right or left.
- R8 interconnects traversing eight blocks to the right or left.
- R24 row interconnects for high-speed access across the length of the device.

The direct link interconnect allows an LAB, DSP block, or TriMatrix memory block to drive into the local interconnect of its left and right neighbors and then back into itself. Only one side of a M-RAM block interfaces with direct link and row interconnects. This provides fast communication between adjacent LABs and/or blocks without using row interconnect resources.

The R4 interconnects span four LABs, three LABs and one M512 RAM block, two LABs and one M4K RAM block, or two LABs and one DSP block to the right or left of a source LAB. These resources are used for fast

can drive other R8 interconnects to extend their range as well as C8 interconnects for row-to-row connections. One R8 interconnect is faster than two R4 interconnects connected together.

R24 row interconnects span 24 LABs and provide the fastest resource for long row connections between LABs, TriMatrix memory, DSP blocks, and IOEs. The R24 row interconnects can cross M-RAM blocks. R24 row interconnects drive to other row or column interconnects at every fourth LAB and do not drive directly to LAB local interconnects. R24 row interconnects drive LAB local interconnects via R4 and C4 interconnects. R24 interconnects can drive R24, R4, C16, and C4 interconnects.

The column interconnect operates similarly to the row interconnect and vertically routes signals to and from LABs, TriMatrix memory, DSP blocks, and IOEs. Each column of LABs is served by a dedicated column interconnect, which vertically routes signals to and from LABs, TriMatrix memory and DSP blocks, and horizontal IOEs. These column resources include:

- LUT chain interconnects within an LAB
- Register chain interconnects within an LAB
- C4 interconnects traversing a distance of four blocks in up and down direction
- C8 interconnects traversing a distance of eight blocks in up and down direction
- C16 column interconnects for high-speed vertical routing through the device

Stratix devices include an enhanced interconnect structure within LABs for routing LE output to LE input connections faster using LUT chain connections and register chain connections. The LUT chain connection allows the combinatorial output of an LE to directly drive the fast input of the LE right below it, bypassing the local interconnect. These resources can be used as a high-speed connection for wide fan-in functions from LE 1 to LE 10 in the same LAB. The register chain connection allows the register output of one LE to connect directly to the register input of the next LE in the LAB for fast shift registers. The Quartus II Compiler automatically takes advantage of these resources to improve utilization and performance. Figure 2–10 shows the LUT chain and register chain interconnects.

Table 2–2. Stratix Device Routing Scheme																	
	Destination																
Source	LUT Chain	Register Chain	Local Interconnect	Direct Link Interconnect	R4 Interconnect	R8 Interconnect	R24 Interconnect	C4 Interconnect	C8 Interconnect	C16 Interconnect	TE	M512 RAM Block	M4K RAM Block	M-RAM Block	DSP Blocks	Column IOE	Row IOE
LUT Chain											\checkmark						
Register Chain											\checkmark						
Local Interconnect											>	~	~	>	~	>	~
Direct Link Interconnect			~														
R4 Interconnect			\checkmark		\checkmark		\checkmark	\checkmark		\checkmark							
R8 Interconnect			\checkmark			\checkmark			\checkmark								
R24 Interconnect					~		~	~		~							
C4 Interconnect			\checkmark		\checkmark			\checkmark									
C8 Interconnect			\checkmark			\checkmark			\checkmark								
C16 Interconnect					~		~	~		~							
LE	>	\checkmark	>	~	~	>		~	<								
M512 RAM Block			~	>	>	~		>	~								
M4K RAM Block			\checkmark	\checkmark	\checkmark	\checkmark		\checkmark	\checkmark								
M-RAM Block								~	<								
DSP Blocks			\checkmark	\checkmark	\checkmark	\checkmark		\checkmark	\checkmark								
Column IOE				\checkmark				\checkmark	\checkmark	\checkmark							
Row IOE				~		\checkmark	~	~	\checkmark	\checkmark							

Table 2–2 shows the Stratix device's routing scheme.

TriMatrix Memory

TriMatrix memory consists of three types of RAM blocks: M512, M4K, and M-RAM blocks. Although these memory blocks are different, they can all implement various types of memory with or without parity, including true dual-port, simple dual-port, and single-port RAM, ROM, and FIFO buffers. Table 2–3 shows the size and features of the different RAM blocks.

Table 2–3. TriMatrix Memory Features (Part 1 of 2)								
Memory Feature	M512 RAM Block (32 × 18 Bits)	M4K RAM Block (128 × 36 Bits)	M-RAM Block (4K × 144 Bits)					
Maximum performance	(1)	(1)	(1)					
True dual-port memory		~	~					
Simple dual-port memory	~	~	~					
Single-port memory	<u> </u>	 Image: A start of the start of	 Image: A start of the start of					
Shift register	✓	✓						
ROM	~	✓	(2)					
FIFO buffer	<u> </u>	 Image: A start of the start of	 Image: A start of the start of					
Byte enable		✓	 Image: A start of the start of					
Parity bits	✓	 	 Image: A start of the start of					
Mixed clock mode	✓	\checkmark	\checkmark					
Memory initialization	✓	\checkmark						
Simple dual-port memory mixed width support	~	~	~					
True dual-port memory mixed width support		~	~					
Power-up conditions	Outputs cleared	Outputs cleared	Outputs unknown					
Register clears	Input and output registers	Input and output registers	Output registers					
Mixed-port read- during-write	Unknown output/old data	Unknown output/old data	Unknown output					

The memory address depths and output widths can be configured as $4,096 \times 1, 2,048 \times 2, 1,024 \times 4, 512 \times 8$ (or 512×9 bits), 256×16 (or 256×18 bits), and 128×32 (or 128×36 bits). The 128×32 - or 36-bit configuration is not available in the true dual-port mode. Mixed-width configurations are also possible, allowing different read and write widths. Tables 2–5 and 2–6 summarize the possible M4K RAM block configurations.

Table 2–5. M4K RAM Block Configurations (Simple Dual-Port)													
Deed Devi	Write Port												
neau ruil	$4\text{K}\times1$	$2K \times 2$	$1K \times 4$	$\textbf{512} \times \textbf{8}$	256 × 16	128 × 32	$\textbf{512} \times \textbf{9}$	256 × 18	128 × 36				
4K × 1	\checkmark	\checkmark	\checkmark	~	\checkmark	\checkmark							
2K × 2	\checkmark	\checkmark	~	~	~	\checkmark							
1K × 4	\checkmark	\checkmark	\checkmark	~	\checkmark	\checkmark							
512 × 8	\checkmark	\checkmark	\checkmark	~	~	\checkmark							
256 × 16	\checkmark	\checkmark	~	~	~	\checkmark							
128 × 32	\checkmark	\checkmark	\checkmark	~	~	\checkmark							
512 × 9							~	~	~				
256 × 18							\checkmark	\checkmark	\checkmark				
128 × 36							\checkmark	\checkmark	\checkmark				

Table 2–6. M4K RAM Block Configurations (True Dual-Port)												
Port A		Port B										
	$4\mathbf{K} \times 1$	2K × 2	$1K \times 4$	512 × 8	256 × 16	512 × 9	256 × 18					
4K × 1	\checkmark	\checkmark	\checkmark	\checkmark	\checkmark							
2K × 2	\checkmark	~	\checkmark	\checkmark	~							
1K × 4	\checkmark	\checkmark	\checkmark	\checkmark	\checkmark							
512 × 8	\checkmark	~	~	\checkmark	~							
256 × 16	\checkmark	~	\checkmark	\checkmark	~							
512 × 9						\checkmark	~					
256 × 18						\checkmark	~					

When the M4K RAM block is configured as a shift register block, you can create a shift register up to 4,608 bits ($w \times m \times n$).

blocks facing to the left, and another 10 possible from the right adjacent LABs for M-RAM blocks facing to the right. For column interfacing, every M-RAM column unit connects to the right and left column lines, allowing each M-RAM column unit to communicate directly with three columns of LABs. Figures 2–21 through 2–23 show the interface between the M-RAM block and the logic array.

Independent Clock Mode

The memory blocks implement independent clock mode for true dualport memory. In this mode, a separate clock is available for each port (ports A and B). Clock A controls all registers on the port A side, while clock B controls all registers on the port B side. Each port, A and B, also supports independent clock enables and asynchronous clear signals for port A and B registers. Figure 2–24 shows a TriMatrix memory block in independent clock mode.



Figure 2–29. DSP Blocks Arranged in Columns

Stratix devices have an I/O interconnect similar to the R4 and C4 interconnect to drive high-fanout signals to and from the I/O blocks. There are 16 signals that drive into the I/O blocks composed of four output enables io_boe [3..0], four clock enables io_bce [3..0], four clocks io_bclk [3..0], and four clear signals io_bclr [3..0]. The pin's datain signals can drive the IO interconnect, which in turn drives the logic array or other I/O blocks. In addition, the control and data signals can be driven from the logic array, providing a slower but more flexible routing resource. The row or column IOE clocks, io_clk [7..0], provide a dedicated routing resource for low-skew, high-speed clocks. I/O clocks are generated from regional, global, or fast regional clocks (see "PLLs & Clock Networks" on page 2–73). Figure 2–62 illustrates the signal paths through the I/O block.





Table 2–28 shows the possible settings for the I/O standards with drive strength control.

Table 2–28. Programmable Drive Strength							
I/O Standard	I_{OH} / I_{OL} Current Strength Setting (mA)						
3.3-V LVTTL	24 (1), 16, 12, 8, 4						
3.3-V LVCMOS	24 (2), 12 (1), 8, 4, 2						
2.5-V LVTTL/LVCMOS	16 (1), 12, 8, 2						
1.8-V LVTTL/LVCMOS	12 (1), 8, 2						
1.5-V LVCMOS	8 (1), 4, 2						
GTL/GTL+ 1.5-V HSTL Class I and II 1.8-V HSTL Class I and II SSTL-3 Class I and II SSTL-2 Class I and II SSTL-18 Class I and II	Support max and min strength						

Notes to Table 2-28:

(1) This is the Quartus II software default current setting.

(2) I/O banks 1, 2, 5, and 6 do not support this setting.

Quartus II software version 4.2 and later will report current strength as "PCI Compliant" for 3.3-V PCI, 3.3-V PCI-X 1.0, and Compact PCI I/O standards.

Stratix devices support series on-chip termination (OCT) using programmable drive strength. For more information, contact your Altera Support Representative.

Open-Drain Output

Stratix devices provide an optional open-drain (equivalent to an opencollector) output for each I/O pin. This open-drain output enables the device to provide system-level control signals (e.g., interrupt and writeenable signals) that can be asserted by any of several devices.

Slew-Rate Control

The output buffer for each Stratix device I/O pin has a programmable output slew-rate control that can be configured for low-noise or highspeed performance. A faster slew rate provides high-speed transitions for high-performance systems. However, these fast transitions may introduce noise transients into the system. A slow slew rate reduces system noise, but adds a nominal delay to rising and falling edges. Each •

For more information on I/O standards supported by Stratix devices, see the *Selectable I/O Standards in Stratix & Stratix GX Devices* chapter of the *Stratix Device Handbook, Volume* 2.

Stratix devices contain eight I/O banks in addition to the four enhanced PLL external clock out banks, as shown in Figure 2–70. The four I/O banks on the right and left of the device contain circuitry to support high-speed differential I/O for LVDS, LVPECL, 3.3-V PCML, and HyperTransport inputs and outputs. These banks support all I/O standards listed in Table 2–31 except PCI I/O pins or PCI-X 1.0, GTL, SSTL-18 Class II, and HSTL Class II outputs. The top and bottom I/O banks support all single-ended I/O standards. Additionally, Stratix devices support four enhanced PLL external clock output banks, allowing clock output capabilities such as differential support for SSTL and HSTL. Table 2–32 shows I/O standard support for each I/O bank.

Table 2–32. I/O Support by Bank (Part 1 of 2)									
I/O Standard	Top & Bottom Banks (3, 4, 7 & 8)	Left & Right Banks (1, 2, 5 & 6)	Enhanced PLL External Clock Output Banks (9, 10, 11 & 12)						
LVTTL	\checkmark	\checkmark	 Image: A set of the set of the						
LVCMOS	\checkmark	\checkmark	~						
2.5 V	\checkmark	\checkmark	~						
1.8 V	\checkmark	\checkmark	~						
1.5 V	\checkmark	\checkmark	~						
3.3-V PCI	\checkmark		~						
3.3-V PCI-X 1.0	\checkmark		~						
LVPECL		\checkmark	~						
3.3-V PCML		\checkmark	~						
LVDS		\checkmark	~						
HyperTransport technology		\checkmark	~						
Differential HSTL (clock inputs)	\checkmark	\checkmark							
Differential HSTL (clock outputs)			~						
Differential SSTL (clock outputs)			~						
3.3-V GTL	~		✓						
3.3-V GTL+	\checkmark	\checkmark	~						
1.5-V HSTL Class I	\checkmark	\checkmark	~						
1.5-V HSTL Class II	\checkmark		~						
1.8-V HSTL Class I	\checkmark	\checkmark	~						
1.8-V HSTL Class II	\checkmark		~						
SSTL-18 Class I	\checkmark	\checkmark	✓						
SSTL-18 Class II	\checkmark		✓						
SSTL-2 Class I	\checkmark	\checkmark	✓						
SSTL-2 Class II	\checkmark	\checkmark	~						
SSTL-3 Class I	\checkmark	\checkmark	✓						

Table 2–32 shows I/O standard support for each I/O bank.

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iadie 4–40. IN512 Block Internal Timing Microparameter Descriptions							
Symbol	Parameter						
t _{M512RC}	Synchronous read cycle time						
t _{M512WC}	Synchronous write cycle time						
t _{M512WERESU}	Write or read enable setup time before clock						
t _{M512WEREH}	Write or read enable hold time after clock						
t _{M512CLKENSU}	Clock enable setup time before clock						
t _{M512CLKENH}	Clock enable hold time after clock						
t _{M512DATASU}	Data setup time before clock						
t _{M512DATAH}	Data hold time after clock						
t _{M512WADDRSU}	Write address setup time before clock						
t _{m512WADDRH}	Write address hold time after clock						
t _{M512RADDRSU}	Read address setup time before clock						
t _{M512RADDRH}	Read address hold time after clock						
t _{M512DATACO1}	Clock-to-output delay when using output registers						
t _{M512DATACO2}	Clock-to-output delay without output registers						
t _{M512CLKHL}	Register minimum clock high or low time. This is a limit on the min time for the clock on the registers in these blocks. The actual performance is dependent upon the internal point-to-point delays in the blocks and may give slower performance as shown in Table 4–36 on page 4–20 and as reported by the timing analyzer in the Quartus II software.						
t _{M512CLR}	Minimum clear pulse width						

Table 4–41. M4K Block Internal Timing Microparameter Descriptions (Part 1 of 2)

Symbol	Parameter
t _{M4KRC}	Synchronous read cycle time
t _{M4KWC}	Synchronous write cycle time
t _{M4KWERESU}	Write or read enable setup time before clock
t _{M4KWEREH}	Write or read enable hold time after clock
t _{M4KCLKENSU}	Clock enable setup time before clock
t _{M4KCLKENH}	Clock enable hold time after clock
t _{M4KBESU}	Byte enable setup time before clock
t _{M4KBEH}	Byte enable hold time after clock
t _{M4KDATAASU}	A port data setup time before clock

Table 4–59. EP1S10 External I/O Timing on Row Pins Using Regional Clock Networks Note (1)											
Parameter	-5 Spee	d Grade	-6 Spee	d Grade	-7 Spee	d Grade	-8 Spee				
	Min	Max	Min	Max	Min	Max	Min	Max	Unit		
t _{INSU}	2.161		2.336		2.685		NA		ns		
t _{INH}	0.000		0.000		0.000		NA		ns		
t _{OUTCO}	2.434	4.889	2.434	5.226	2.434	5.643	NA	NA	ns		
t _{xz}	2.461	4.493	2.461	5.282	2.461	5.711	NA	NA	ns		
t _{ZX}	2.461	4.493	2.461	5.282	2.461	5.711	NA	NA	ns		
t _{INSUPLL}	1.057		1.172		1.315		NA		ns		
t _{INHPLL}	0.000		0.000		0.000		NA		ns		
t _{OUTCOPLL}	1.327	2.773	1.327	2.848	1.327	2.940	NA	NA	ns		
t _{XZPLL}	1.354	2.827	1.354	2.904	1.354	3.008	NA	NA	ns		
t _{ZXPLL}	1.354	2.827	1.354	2.904	1.354	3.008	NA	NA	ns		

Table 4–60. EP1S10 External I/O Timing on Row Pins Using Global Clock Networks Note (1)									
Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		1114
	Min	Max	Min	Max	Min	Max	Min	Max	Unit
t _{INSU}	1.787		1.944		2.232		NA		ns
t _{INH}	0.000		0.000		0.000		NA		ns
t _{OUTCO}	2.647	5.263	2.647	5.618	2.647	6.069	NA	NA	ns
t _{xz}	2.674	5.317	2.674	5.674	2.674	6.164	NA	NA	ns
t _{ZX}	2.674	5.317	2.674	5.674	2.674	6.164	NA	NA	ns
t _{INSUPLL}	1.371		1.1472		1.654		NA		ns
t _{INHPLL}	0.000		0.000		0.000		NA		ns
t _{OUTCOPLL}	1.144	2.459	1.144	2.548	1.144	2.601	NA	NA	ns
t _{XZPLL}	1.171	2.513	1.171	2.604	1.171	2.669	NA	NA	ns
t ^{ZXPLL}	1.171	2.513	1.171	2.604	1.171	2.669	NA	NA	ns

Note to Tables 4–55 *to* 4–60:

(1) Only EP1S25, EP1S30, and EP1S40 have speed grade of -8.

Tables 4–91 through 4–96 show the external timing parameters on column and row pins for EP1S80 devices.

Table 4–91. EP1S80 External I/O Timing on Column Pins Using Fast Regional Clock Networks Note (1)									
Demonstern	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		11
Farailieler	Min	Max	Min	Max	Min	Max	Min	Max	Unit
t _{INSU}	2.328		2.528		2.900		NA		ns
t _{INH}	0.000		0.000		0.000		NA		ns
t _{OUTCO}	2.422	4.830	2.422	5.169	2.422	5.633	NA	NA	ns
t _{xz}	2.362	4.704	2.362	5.037	2.362	5.509	NA	NA	ns
t _{ZX}	2.362	4.704	2.362	5.037	2.362	5.509	NA	NA	ns

Table 4–92. EP1S80 External I/O Timing on Column Pins Using Regional Clock Networks Note (1)									
Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		1114
	Min	Max	Min	Max	Min	Max	Min	Max	Unit
t _{INSU}	1.760		1.912		2.194		NA		ns
t _{INH}	0.000		0.000		0.000		NA		ns
t _{OUTCO}	2.761	5.398	2.761	5.785	2.761	6.339	NA	NA	ns
t _{XZ}	2.701	5.272	2.701	5.653	2.701	6.215	NA	NA	ns
t _{ZX}	2.701	5.272	2.701	5.653	2.701	6.215	NA	NA	ns
t _{INSUPLL}	0.462		0.606		0.785		NA		ns
t _{INHPLL}	0.000		0.000		0.000		NA		ns
t _{OUTCOPLL}	1.661	2.849	1.661	2.859	1.661	2.881	NA	NA	ns
t _{XZPLL}	1.601	2.723	1.601	2.727	1.601	2.757	NA	NA	ns
t _{ZXPLL}	1.601	2.723	1.601	2.727	1.601	2.757	NA	NA	ns

FPLL[107]CLK Pins in Wire-Bond Packages (Part 2 of 2)							
I/O Standard	-6 Speed Grade	-7 Speed Grade	-8 Speed Grade	Unit			
LVCMOS	422	390	390	MHz			
GTL+	250	200	200	MHz			
SSTL-3 Class I	350	300	300	MHz			
SSTL-3 Class II	350	300	300	MHz			
SSTL-2 Class I	350	300	300	MHz			
SSTL-2 Class II	350	300	300	MHz			
SSTL-18 Class I	350	300	300	MHz			
SSTL-18 Class II	350	300	300	MHz			
1.5-V HSTL Class I	350	300	300	MHz			
1.8-V HSTL Class I	350	300	300	MHz			
CTT	250	200	200	MHz			
Differential 1.5-V HSTL C1	350	300	300	MHz			
LVPECL (1)	717	640	640	MHz			
PCML (1)	375	350	350	MHz			
LVDS (1)	717	640	640	MHz			
HyperTransport technology (1)	717	640	640	MHz			

Table A 110 Strativ Maximum Innut Clock Rate for CLKIN 2 9 111 Pins &

Table 4–119. Stratix Maximum Input Clock Rate for CLK[1, 3, 8, 10] Pins in Wire-Bond Packages (Part 1 of 2)

I/O Standard	-6 Speed Grade	-7 Speed Grade	-8 Speed Grade	Unit
LVTTL	422	390	390	MHz
2.5 V	422	390	390	MHz
1.8 V	422	390	390	MHz
1.5 V	422	390	390	MHz
LVCMOS	422	390	390	MHz
GTL+	250	200	200	MHz
SSTL-3 Class I	350	300	300	MHz
SSTL-3 Class II	350	300	300	MHz
SSTL-2 Class I	350	300	300	MHz
SSTL-2 Class II	350	300	300	MHz

Table 4–130. Enhanced PLL Specifications for -8 Speed Grade (Part 2 of 3)							
Symbol	Parameter	Min	Тур	Мах	Unit		
t _{EINJITTER}	External feedback clock period jitter			±200 <i>(3)</i>	ps		
t _{FCOMP}	External feedback clock compensation time (4)			6	ns		
f _{OUT}	Output frequency for internal global or regional clock	0.3		357	MHz		
f _{OUT_EXT}	Output frequency for external clock (3)	0.3		369	MHz		
toutduty	Duty cycle for external clock output (when set to 50%)	45		55	%		
t _{JITTER}	Period jitter for external clock output (6)			±100 ps for >200-MHz outclk ±20 mUI for <200-MHz outclk	ps or mUI		
t _{CONFIG5,6}	Time required to reconfigure the scan chains for PLLs 5 and 6			289/f _{SCANCLK}			
t _{CONFIG11,12}	Time required to reconfigure the scan chains for PLLs 11 and 12			193/f _{SCANCLK}			
t _{SCANCLK}	scanclk frequency (5)			22	MHz		
t _{DLOCK}	Time required to lock dynamically (after switchover or reconfiguring any non-post-scale counters/delays) (7) (11)	(9)		100	μs		
t _{LOCK}	Time required to lock from end of device configuration (11)	10		400	μs		
f _{VCO}	PLL internal VCO operating range	300		600 (8)	MHz		

Table 4–133. Fast PLL Specifications for -8 Speed Grades (Part 2 of 2)							
Symbol	Parameter	Min	Max	Unit			
t _{ARESET}	Minimum pulse width on areset signal	10		ns			

Notes to Tables 4–131 through 4–133:

(1) See "Maximum Input & Output Clock Rates" on page 4–76.

- (2) PLLs 7, 8, 9, and 10 in the EP1S80 device support up to 717-MHz input and output.
- (3) Use this equation ($f_{OUT} = f_{IN} * ml(n \times \text{post-scale counter})$) in conjunction with the specified f_{INPFD} and f_{VCO} ranges to determine the allowed PLL settings.
- (4) When using the SERDES, high-speed differential I/O mode supports a maximum output frequency of 210 MHz to the global or regional clocks (that is, the maximum data rate 840 Mbps divided by the smallest SERDES J factor of 4).
- (5) Refer to the section "High-Speed I/O Specification" on page 4-87 for more information.
- (6) This parameter is for high-speed differential I/O mode only.
- (7) These counters have a maximum of 32 if programmed for 50/50 duty cycle. Otherwise, they have a maximum of 16.
- (8) High-speed differential I/O mode supports W = 1 to 16 and J = 4, 7, 8, or 10.

DLL Specifications

Table 4–134 reports the jitter for the DLL in the DQS phase shift reference circuit.

Table 4–134. DLL Jitter for DQS Phase Shift Reference Circuit						
Frequency (MHz)	DLL Jitter (ps)					
197 to 200	± 100					
160 to 196	± 300					
100 to 159	± 500					

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For more information on DLL jitter, see the *DDR SRAM* section in the *Stratix Architecture* chapter of the *Stratix Device Handbook, Volume* 1.

Table 4–135 lists the Stratix DLL low frequency limit for full phase shift across all PVT conditions. The Stratix DLL can be used below these frequencies, but it will not achieve the full phase shift requested across all